



# STW6NA80 STH6NA80FI

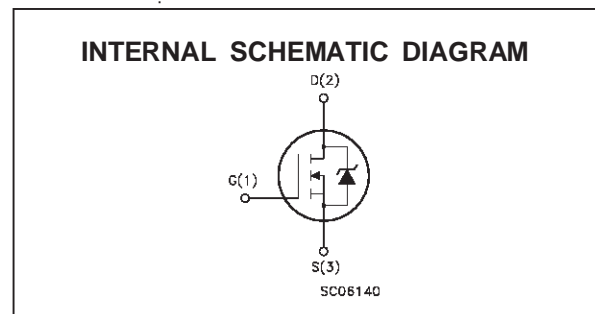
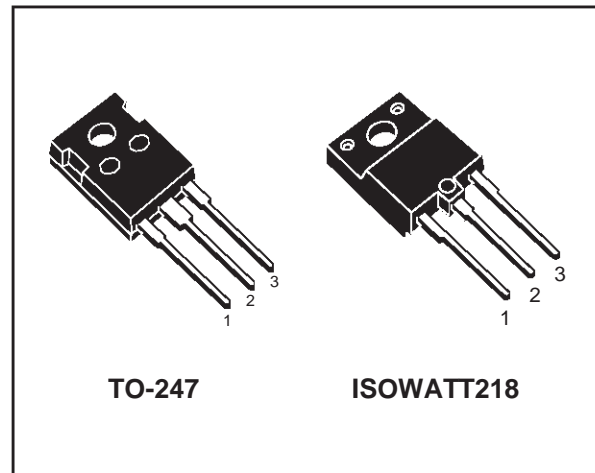
## N - CHANNEL 800V - 1.8Ω - 5.4A - TO-247/ISOWATT218 FAST POWER MOS TRANSISTOR

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STW6NA80	800 V	< 2.2 Ω	5.4 A
STH6NA80FI	800 V	< 2.2 Ω	3.4 A

- TYPICAL R<sub>DS(on)</sub> = 1.8 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- VERY HIGH CURRENT CAPABILITY
- APPLICATION ORIENTED CHARACTERIZATION

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- REGULATORS
- DC-DC & DC-AC CONVERTERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMPDRIVERS, Etc.)



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW6NA80	STH6NA80FI	
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	800		V
V <sub>DGR</sub>	Drain- gate Voltage (R <sub>GS</sub> = 20 kΩ)	800		V
V <sub>GS</sub>	Gate-source Voltage	± 30		V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	5.4	3.4	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	3.4	2.1	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	22	22	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	150	60	W
	Derating Factor	1.2	0.48	W/°C
V <sub>ISO</sub>	Insulation Withstand Voltage (DC)	—	4000	V
T <sub>stg</sub>	Storage Temperature	-65 to 150		°C
T <sub>j</sub>	Max. Operating Junction Temperature	150		°C

(●) Pulse width limited by safe operating area

## STW6NA80-STH6NA80FI

### THERMAL DATA

		TO-247	ISOWATT218		
R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	0.83	2.08	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	30		°C/W
R <sub>thc-sink</sub>	Thermal Resistance Case-sink	Typ	0.1		°C/W
T <sub>l</sub>	Maximum Lead Temperature For Soldering Purpose		300		°C

### AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T <sub>j</sub> max, δ < 1%)	5.4	A
E <sub>AS</sub>	Single Pulse Avalanche Energy (starting T <sub>j</sub> = 25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V)	150	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (pulse width limited by T <sub>j</sub> max, δ < 1%)	5.8	mJ
I <sub>AR</sub>	Avalanche Current, Repetitive or Not-Repetitive (T <sub>c</sub> = 100 °C, pulse width limited by T <sub>j</sub> max, δ < 1%)	3.4	A

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

#### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	800			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating x 0.8 T <sub>c</sub> = 100 °C			25 50	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 30 V			± 100	nA

#### ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	2.25	3	3.75	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 3 A V <sub>GS</sub> = 10 V I <sub>D</sub> = 3 A T <sub>c</sub> = 100 °C		1.8	2.2 4.4	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> V <sub>GS</sub> = 10 V	5.4			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)max</sub> I <sub>D</sub> = 3 A	3	5.5		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1250	1700	pF
C <sub>oss</sub>	Output Capacitance			140	190	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			35	50	pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 400\text{ V}$ $I_D = 3\text{ A}$		40	55	ns
$t_r$	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 3)		100	135	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 640\text{ V}$ $I_D = 6\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		180		A/ $\mu\text{s}$
$Q_g$	Total Gate Charge	$V_{DD} = 640\text{ V}$ $I_D = 6\text{ A}$ $V_{GS} = 10\text{ V}$		55	75	nC
$Q_{gs}$	Gate-Source Charge			8		nC
$Q_{gd}$	Gate-Drain Charge			24		nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off-voltage Rise Time	$V_{DD} = 640\text{ V}$ $I_D = 6\text{ A}$		75	100	ns
$t_f$	Fall Time	$R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$ (see test circuit, figure 5)		25	35	ns
$t_c$	Cross-over Time			110	150	ns

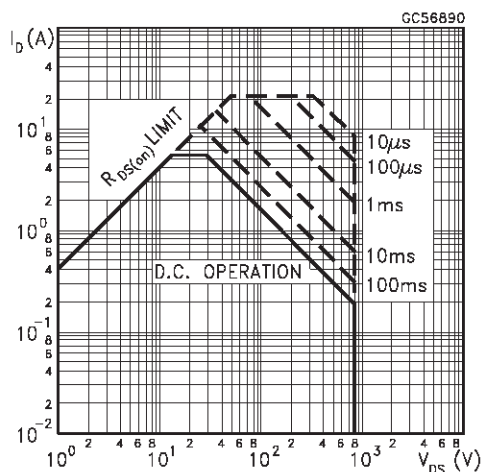
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain Current				5.4	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				22	A
$V_{SD}(\ast)$	Forward On Voltage	$I_{SD} = 6\text{ A}$ $V_{GS} = 0$			1.6	V
$t_{rr}$	Reverse Recovery Time	$I_{SD} = 6\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$ (see test circuit, figure 5)		800		ns
$Q_{rr}$	Reverse Recovery Charge			15.2		$\mu\text{C}$
$I_{RRM}$	Reverse Recovery Current			38		A

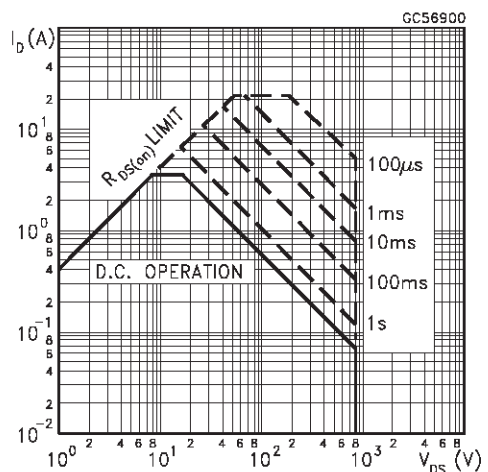
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(•) Pulse width limited by safe operating area

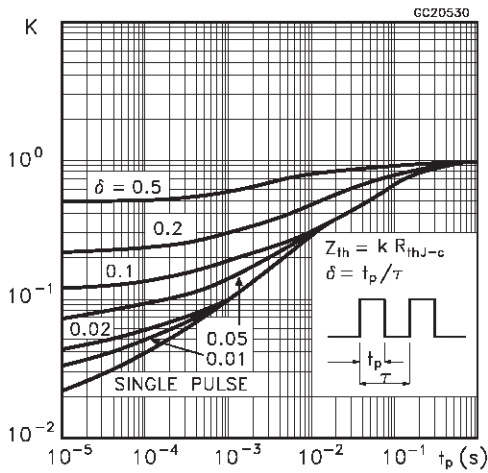
Safe Operating Area for TO-247



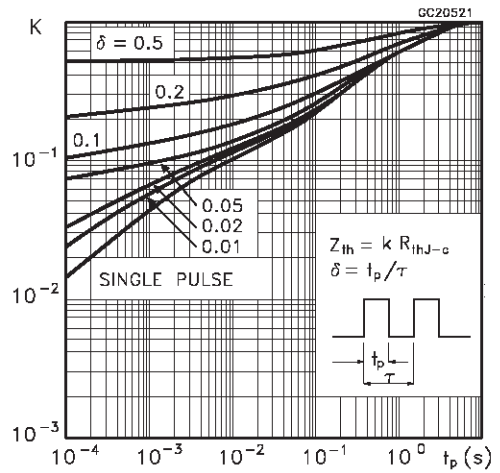
Safe Operating Area for ISOWATT218



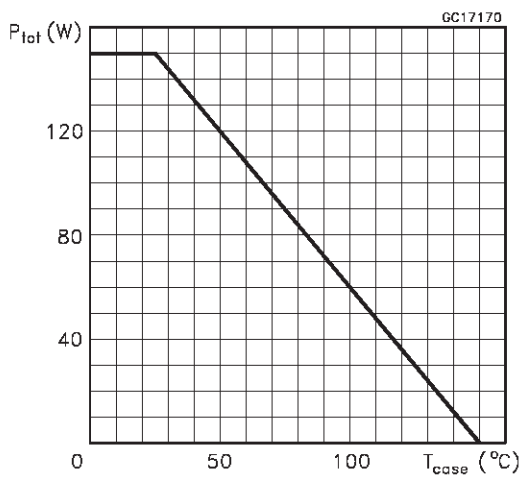
Thermal Impedance for TO-247



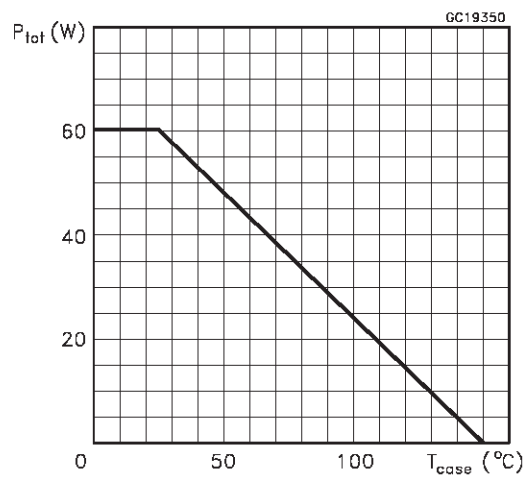
Thermal Impedance for ISOWATT218



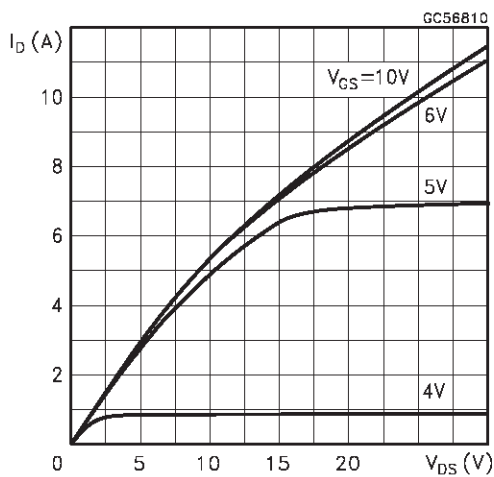
Derating Curve for TO-247



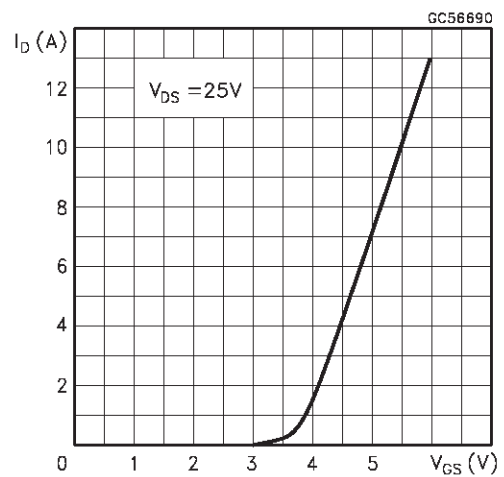
Derating Curve for ISOWATT218



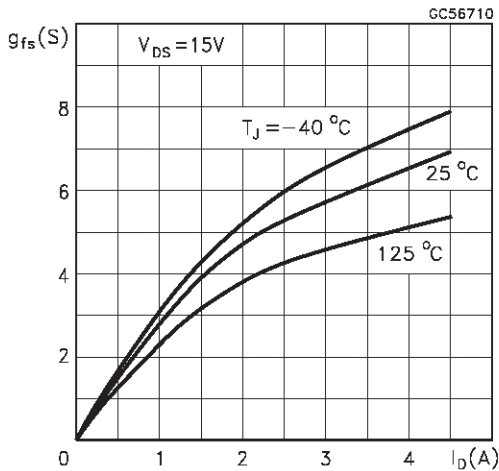
Output Characteristics



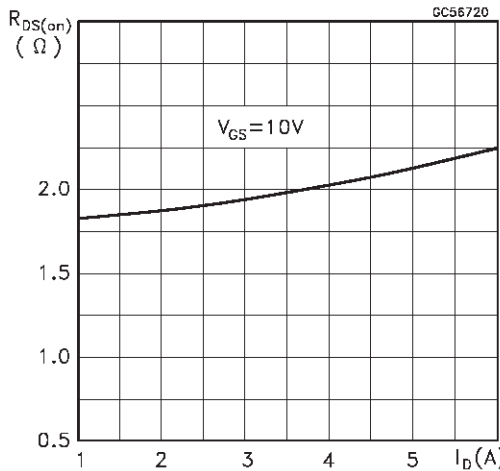
Transfer Characteristics



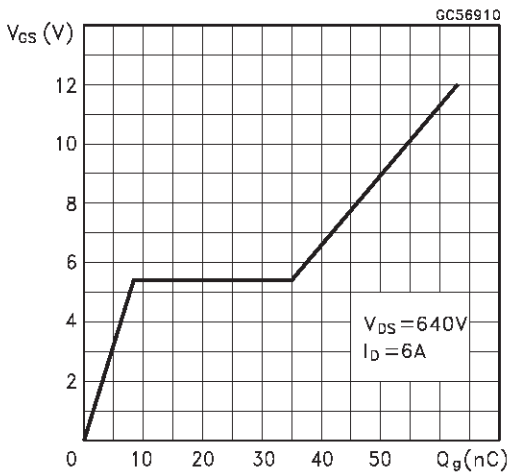
Transconductance



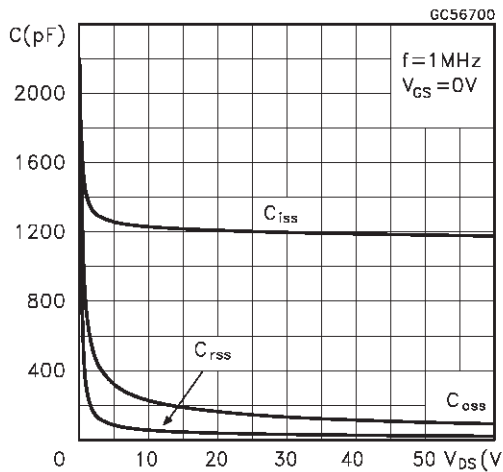
Static Drain-source On Resistance



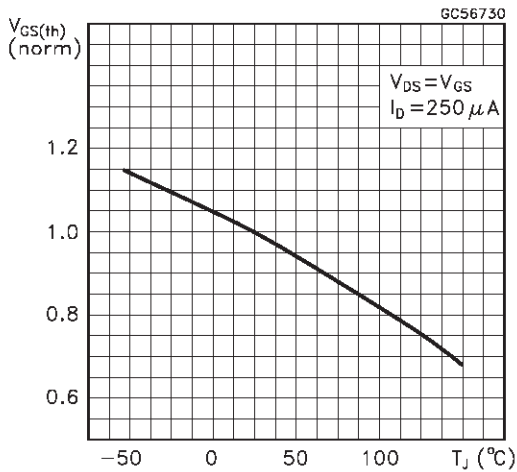
Gate Charge vs Gate-source Voltage



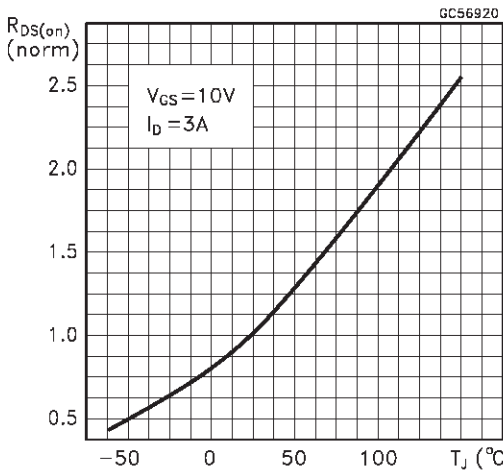
Capacitance Variations



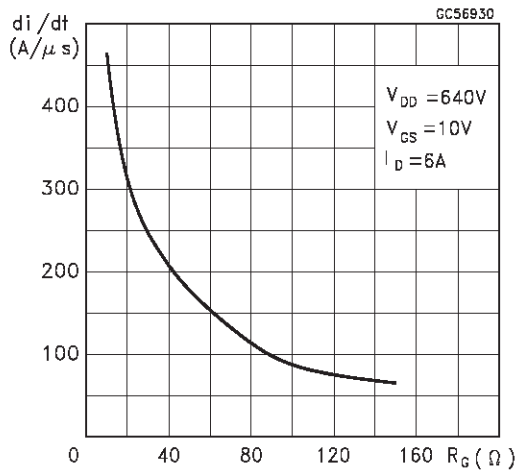
Normalized Gate Threshold Voltage vs Temperature



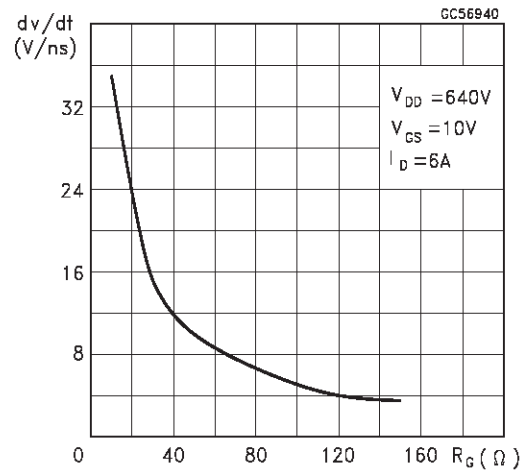
Normalized On Resistance vs Temperature



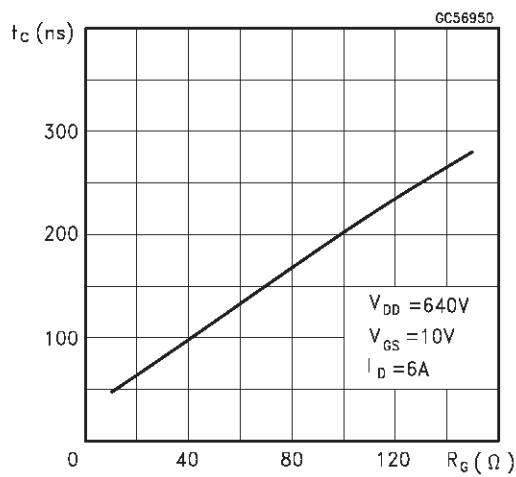
Turn-on Current Slope



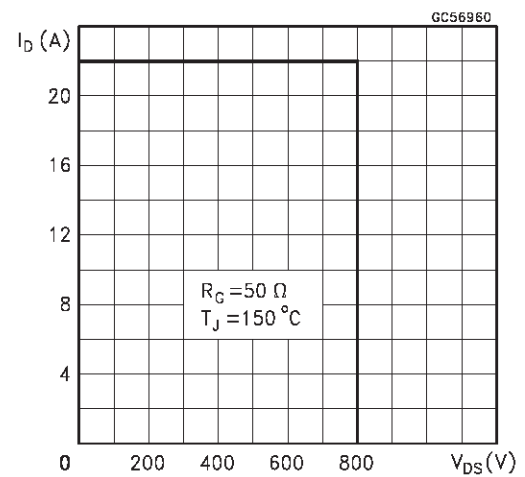
Turn-off Drain-source Voltage Slope



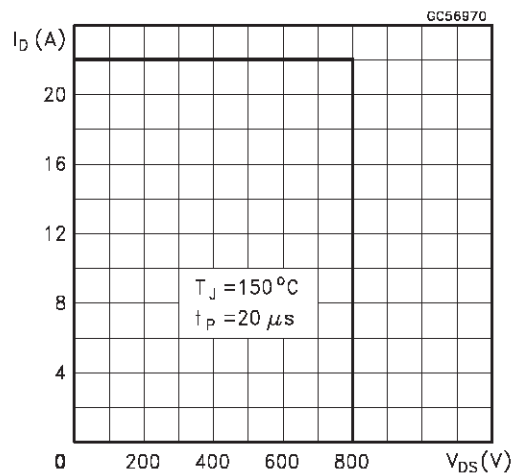
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

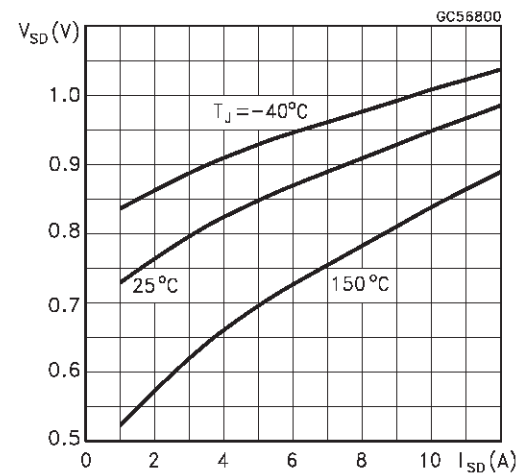


Fig. 1: Unclamped Inductive Load Test Circuit

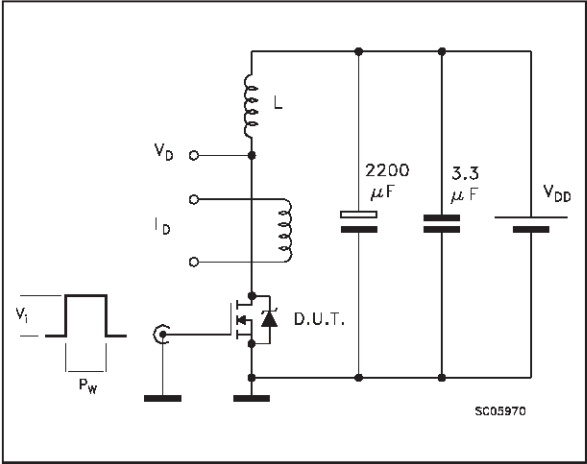


Fig. 2: Unclamped Inductive Waveform

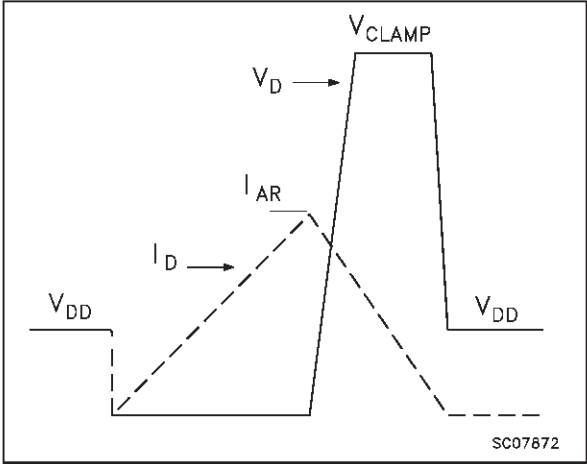


Fig. 3: Switching Times Test Circuits For Resistive Load

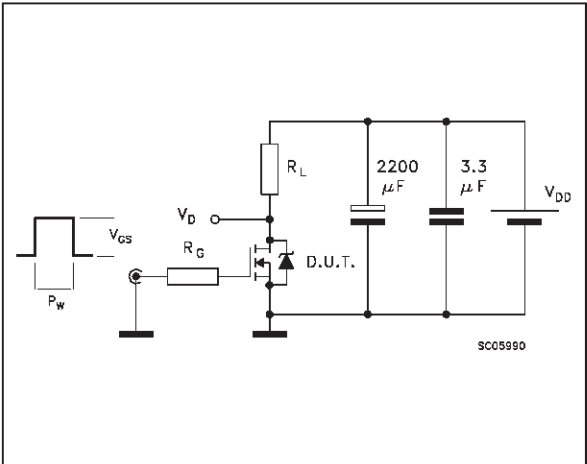


Fig. 4: Gate Charge test Circuit

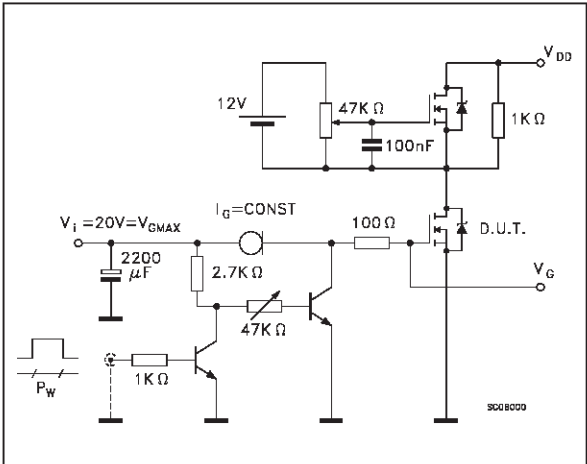
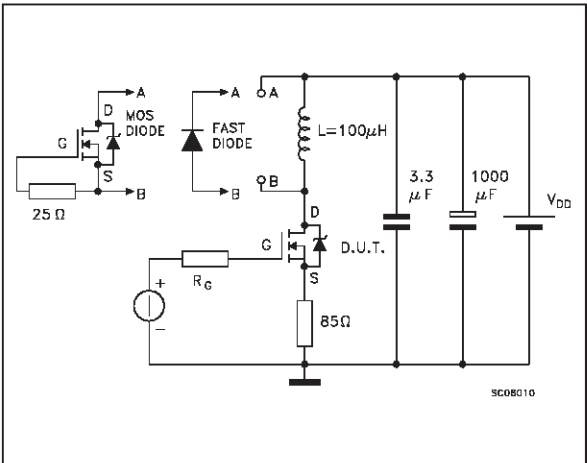
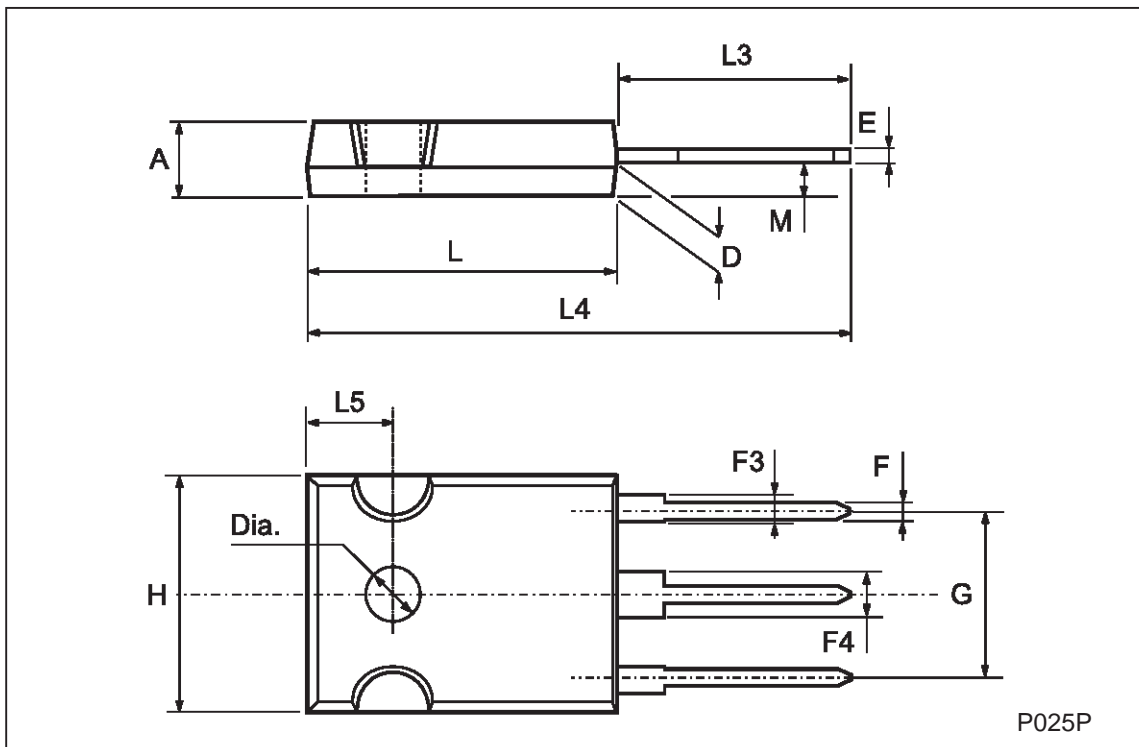


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

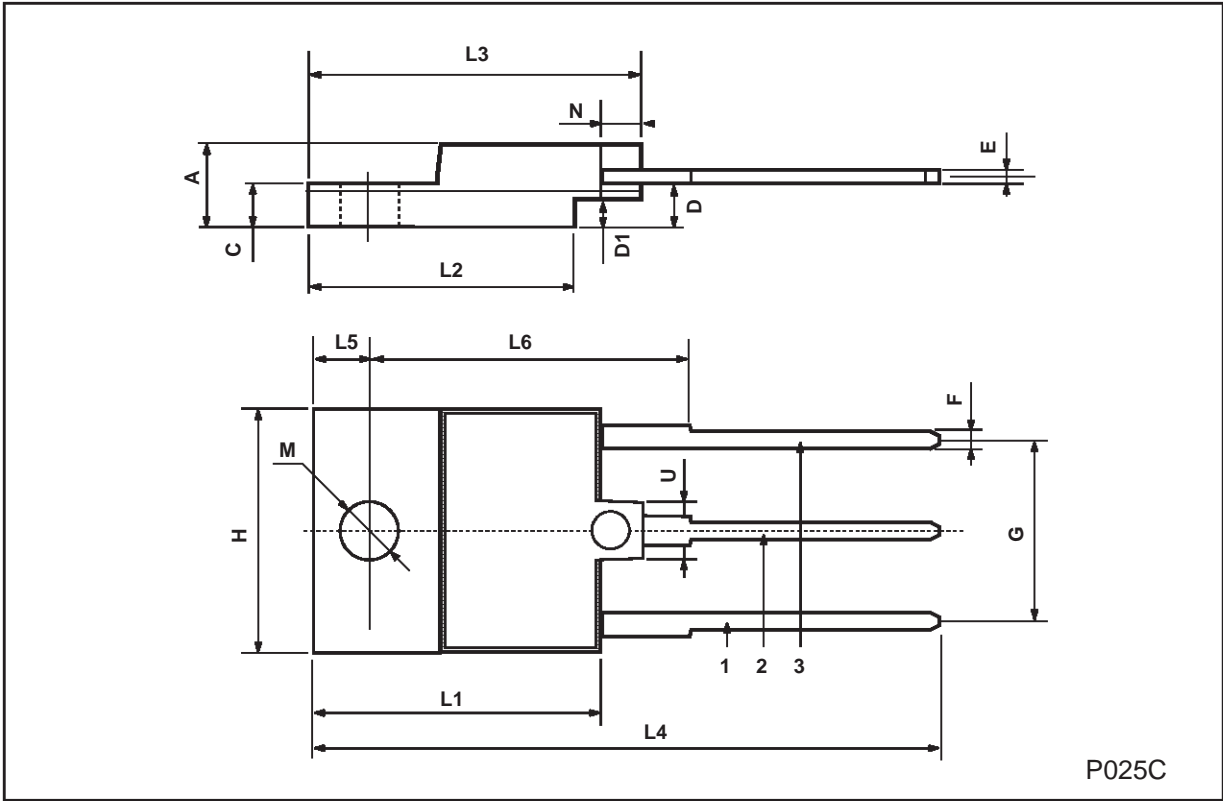
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559	0.413	0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118
Dia	3.55		3.65	0.140		0.144





**ISOWATT218 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.210		0.222
C	3.3		3.8	0.130		0.149
D	2.9		3.1	0.114		0.122
D1	1.88		2.08	0.074		0.081
E	0.75		1	0.029		0.039
F	1.05		1.25	0.041		0.049
G	10.8		11.2	0.425		0.441
H	15.8		16.2	0.622		0.637
L1	20.8		21.2	0.818		0.834
L2	19.1		19.9	0.752		0.783
L3	22.8		23.6	0.897		0.929
L4	40.5		42.5	1.594		1.673
L5	4.85		5.25	0.190		0.206
L6	20.25		20.75	0.797		0.817
M	3.5		3.7	0.137		0.145
N	2.1		2.3	0.082		0.090
U		4.6			0.181	



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